DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$ Max	I_D Max T_A = +25°C
60V	8Ω @ V_{GS} = 5V	170mA
	6Ω @ V_{GS} = 10V	200mA

Features and Benefits

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- ESD Protected Gate, 1KV (HBM)
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at https://www.diodes.com/products/automotive/automotive-products/.**
- **This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability. https://www.diodes.com/quality/product-definitions/**
- **An Automotive-Compliant Part is Available Under Separate Datasheet (DMN65D8LDWQ)**

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

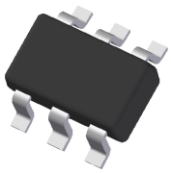
- DC-DC Converters
- Power Management Functions
- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.

Mechanical Data

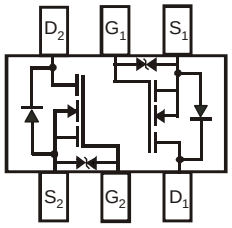
- Case: SOT363 (Standard)
- Case Material: Molded Plastic; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Solderable per MIL-STD-202, Method 208 e3
- Lead Free Plating (Matte Tin Finish Annealed over Alloy 42 Lead-Frame).
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)

ESD PROTECTED TO 1kV

SOT363 (Standard)



Top View



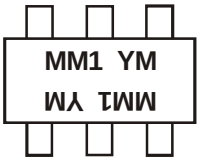
Top View
Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN65D8LDW-7	SOT363 (Standard)	3,000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



MM1= Product Type Marking Code
YM = Date Code Marking
Y or $\overline{Y}$ = Year (ex: I = 2021)
M or $\overline{M}$= Month (ex: 9 = September)

Date Code Key

Year	2007	……	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	U	……	I	J	K	L	M	N	O	P	R	S

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic				Symbol	Value	Units
Drain-Source Voltage				V_{DSS}	60	V
Gate-Source Voltage				V_{GSS}	±20	V
Continuous Drain Current (Note 5)	V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	180 140	mA
Continuous Drain Current (Note 5)	V_{GS} = 5V	Steady State	T_A = +25°C T_A = +70°C	I_D	150 120	mA
Continuous Drain Current (Note 6)	V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	200 160	mA
Continuous Drain Current (Note 6)	V_{GS} = 5V	Steady State	T_A = +25°C T_A = +70°C	I_D	170 140	mA
Pulsed Drain Current (10µs pulse, duty cycle = 1%)				I_{DM}	800	mA

Thermal Characteristics

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P_D	300	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	435	°C/W
Total Power Dissipation (Note 6)	P_D	400	mW
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	330	°C/W
Thermal Resistance, Junction to Case (Note 6)	$R_{\theta JC}$	139	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current T_J = +25°C T_J = +125°C (Note 8)	I_{DSS}	—	—	1.0 5.0	µA	V_{DS} = 60V, V_{GS} = 0V
Gate-Body Leakage	I_{GSS}	—	—	±5.0	µA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	1.0	—	2.0	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	—	2.2	8	Ω	V_{GS} = 5V, I_D = 0.115A
		—	2.0	6	Ω	V_{GS} = 10V, I_D = 0.115A
Forward Transconductance	g_{FS}	80	—	—	mS	V_{DS} = 10V, I_D = 0.115A
Diode Forward Voltage	V_{SD}	—	0.8	1.2	V	V_{GS} = 0V, I_S = 115mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	22.0	—	pF	V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	3.2	—		
Reverse Transfer Capacitance	C_{rss}	—	2.0	—		
Gate Resistance	R_G	—	79.9	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
Total Gate Charge V_{GS} = 10V	Q_g	—	0.87	—	nC	V_{GS} = 10V, V_{DS} = 30V, I_D = 150mA
Total Gate Charge V_{GS} = 4.5V	Q_g	—	0.43	—		
Gate-Source Charge	Q_{gs}	—	0.11	—		
Gate-Drain Charge	Q_{gd}	—	0.11	—		
Turn-On Delay Time	$t_{D(on)}$	—	3.3	—	nS	V_{DD} = 30V, I_D = 0.115A, V_{GEN} = 10V, R_{GEN} = 25Ω
Turn-On Rise Time	t_r	—	3.2	—		
Turn-Off Delay Time	$t_{D(off)}$	—	12.0	—		
Turn-Off Fall Time	t_f	—	6.3	—		

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper pad layout
7 .Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

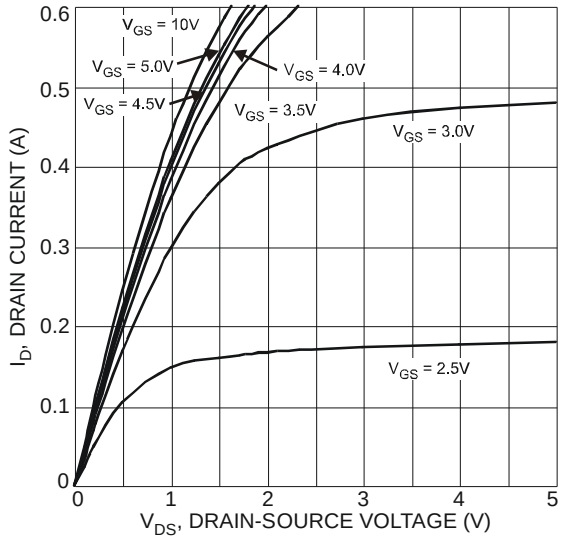


Fig.1 Typical Output Characteristic

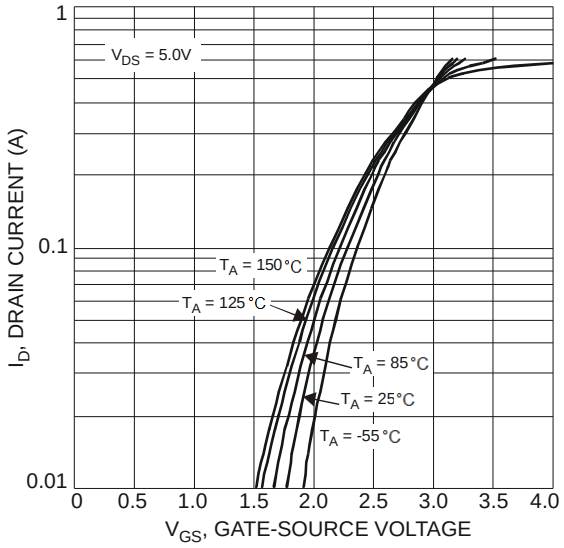


Fig.2 Typical Transfer Characteristics

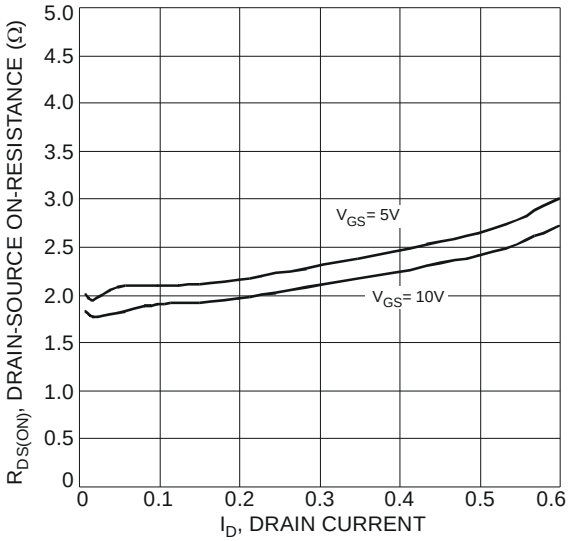


Fig. 3 Typical On-Resistance vs. Drain Current and Temperature

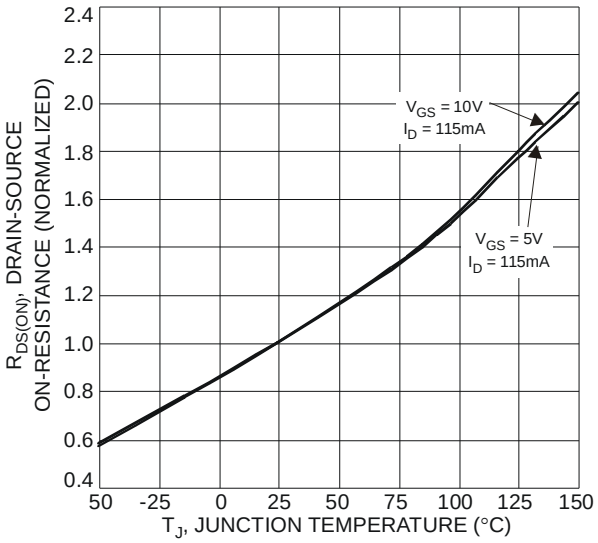


Fig. 4 On-Resistance Variation with Temperature

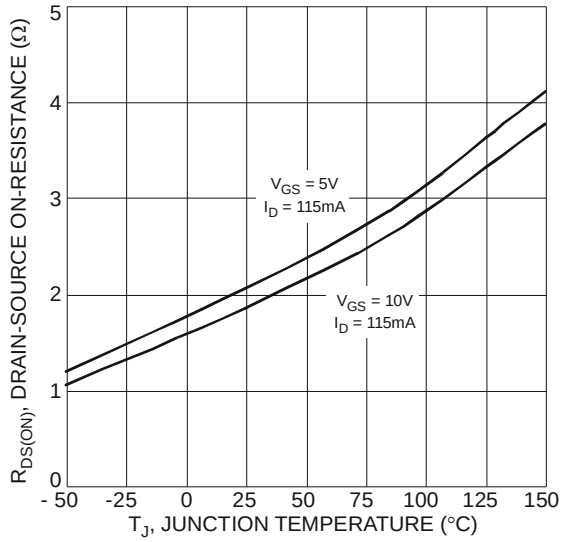


Fig. 5 On-Resistance Variation with Temperature

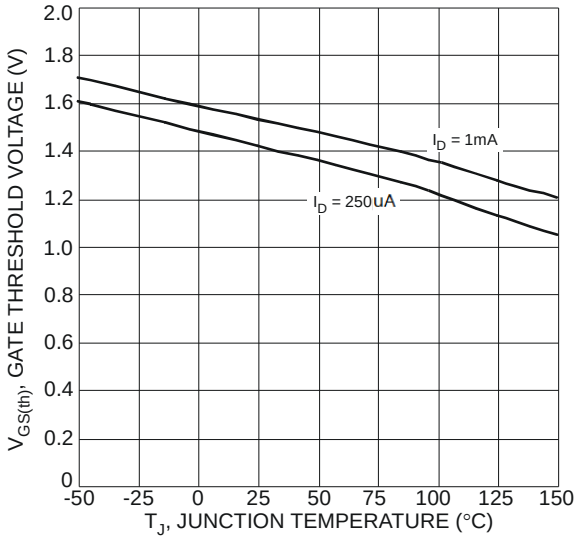


Fig. 6 Gate Threshold Variation vs. Ambient Temperature

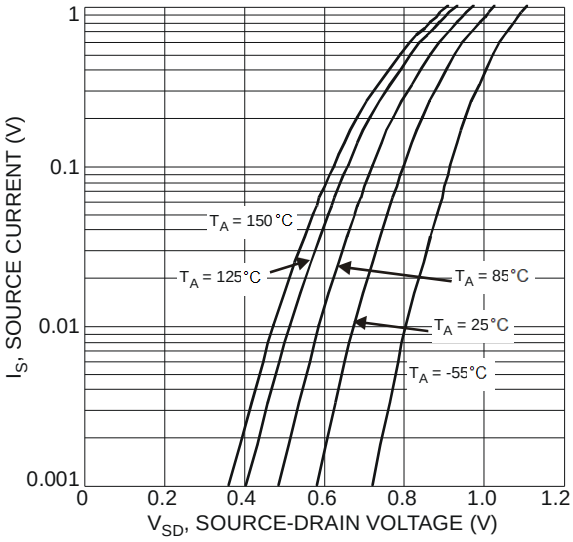


Fig. 7 Diode Forward Voltage vs. Current

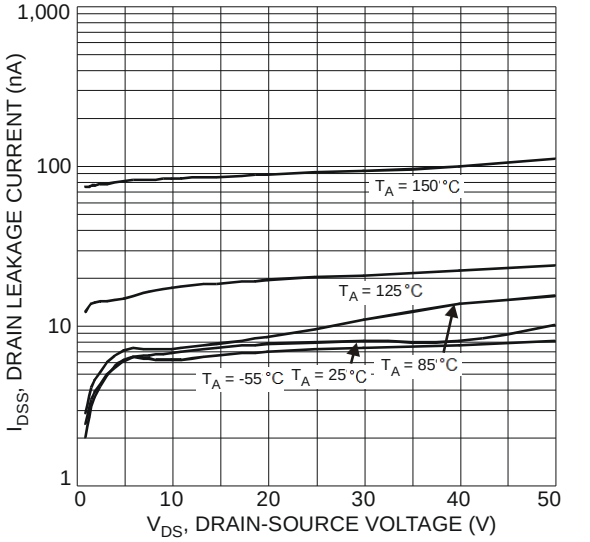


Fig. 8 Typical Drain-Source Leakage Current vs. Voltage

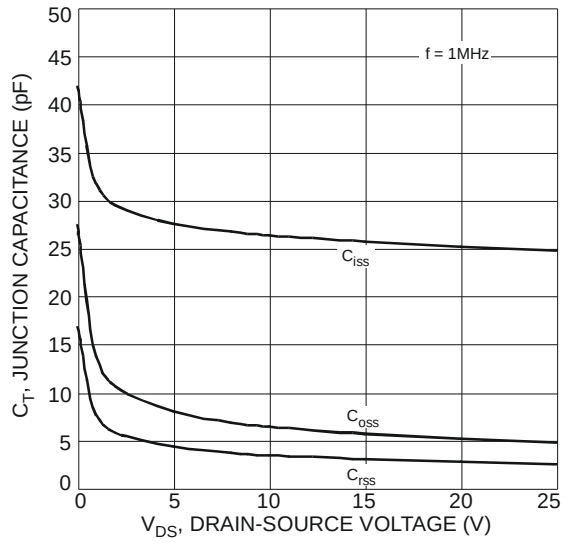


Fig. 9 Typical Junction Capacitance

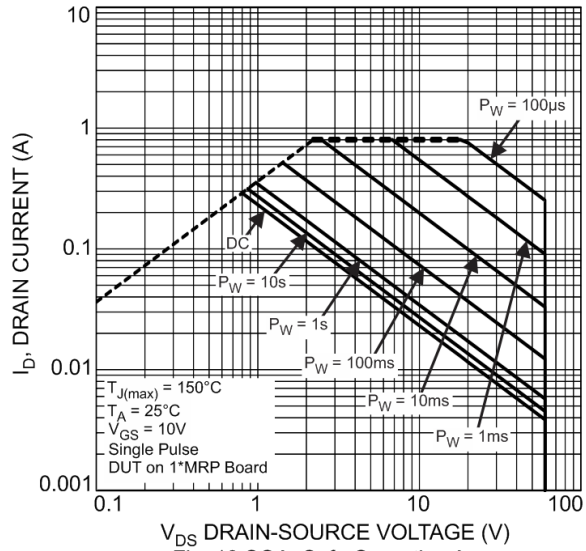


Fig. 10 SOA, Safe Operation Area

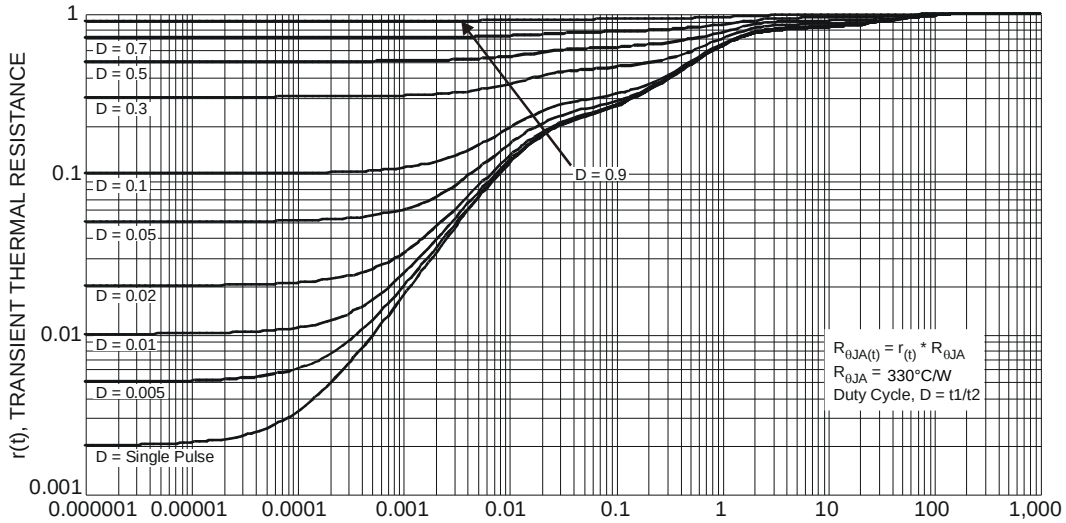
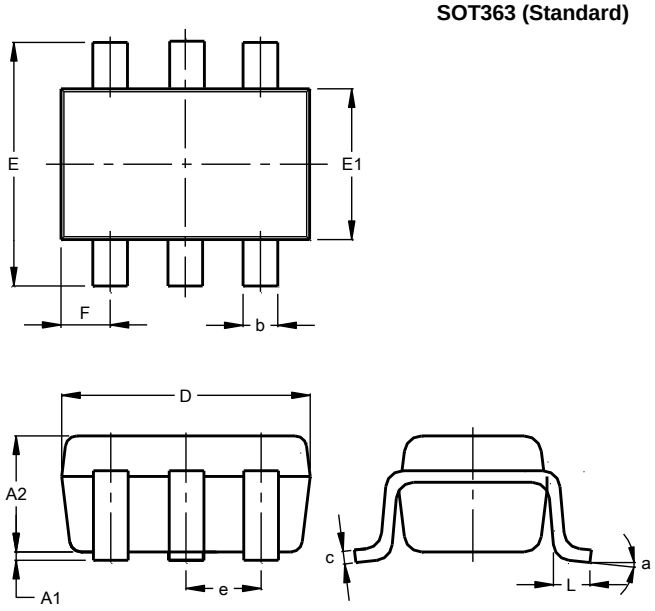


Fig. 11 Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT363 (Standard)

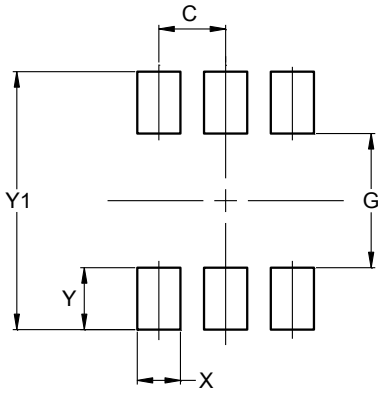


SOT363 (Standard)			
Dim	**Min**	**Max**	**Typ**
A1	0.00	0.10	0.05
A2	0.80	1.00	0.90
b	0.10	0.35	0.225
c	0.08	0.22	0.15
D	1.80	2.20	2.00
E	2.00	2.45	2.225
E1	1.15	1.35	1.25
e	--	--	0.65
F	0.25	0.45	0.35
L	0.25	0.46	0.355
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT363 (Standard)



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500

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